

NIR/Red Enhanced 6 mm² Photodiode-Preamplifier



FEATURES

- Large Active Area
- Low Noise
- High Sensitivity
- Custom Gains Available
- Hermetically Sealed TO-39

Electro-Optical Characteristics at 23°C

Parameters	Test Conditions	Min	Тур	Max	Units
Active Area	3.30 mm x 1.78 mm		5.87		mm ²
Dark Offset	$V_s = \pm 5 V$		1.2	±2	mV
Dark Offset Noise	V _s = ±5 BW = 0.1 to 1000 kHz		198	250	μV rms
Sensitivity	V _s = ±5 V λ = 940 nm	55	63		V/µW
Frequency Response (-3 db)	$V_s = \pm 5 V$	900	1000		Hz
NEP	λ = 940 nm		30		fW/√Hz
Transimpedance Gain			100		MΩ
Supply Current			850	950	μA

Absolute Ratings

Parameters	Units		
Voltage Supply Range +V to –V*	5 to 15 V		
Power Dissipation	15 mW		
Storage and Operating Temperature	–25 to + 100°C		
Soldering Temperature (1/16" from case for 3 seconds max)	+260°C		

*Voltage supply across the device requires a minimum of 5 V to a maximum of 15 V from +V to -V.



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50 MIN

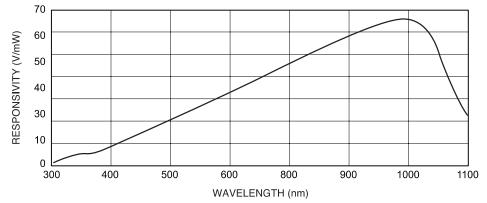
- .028

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.163

ø.018

Typical Spectral Response



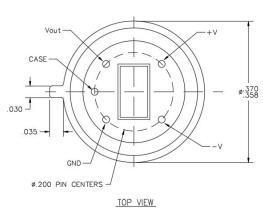
.085 DETECTOR PLANE

Ø.325

GLASS .012 HIGH MAX.

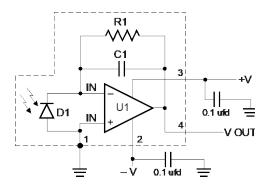
ø.260

Package Information





Dimensions are in inch [metric] units.



Specifications are subject to change without prior notice.